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Fairchild Semiconductor BDW23TU

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BDW23/A/B/C

Hammer Drivers, Audio Amplifiers Applications

- Power Darlington TR
- Complement to BDW24, BDW24A, BDW24B and BDW24C respectively



1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage		
	: BDW23	45	V
	: BDW23A	60	V
	: BDW23B	80	V
	: BDW23C	100	V
V_{CEO}	Collector-Emitter Voltage		
	: BDW23	45	V
	: BDW23A	60	V
	: BDW23B	80	V
	: BDW23C	100	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current (DC)	6	Α
I _{CP}	*Collector Current (Pulse)	8	Α
I _B	Base Current	0.2	Α
P _C	Collector Dissipation (T _C =25°C)	50	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 65 ~ 150	°C

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Electrical Characteristics T_C=25°C unless otherwise noted Unit **Symbol Test Condition** Min. Тур. Max. s V_{CEO}(sus) Collector-Emitter Sustaining Voltage : BDW23 ٧ $I_C = 100 \text{mA}, I_B = 0$ 45 V : BDW23A 60 : BDW23B 80 ٧ ٧ : BDW23C 100 Collector Cut-off Current I_{CBO} $V_{CB} = 45V, I_{E} = 0$ $V_{CB} = 60V, I_{E} = 0$: BDW23 200 μΑ : BDW23A 200 $\mu \mathsf{A}$ $V_{CB} = 80V, I_{E} = 0$ $V_{CB} = 100V, I_{E} = 0$: BDW23B 200 μΑ : BDW23C 200 μΑ Collector Cut-off Current I_{CEO} $V_{CE} = 22V, I_{B} = 0$ $V_{CE} = 30V, I_{B} = 0$: BDW23 500 μΑ 500 : BDW23A μΑ $V_{CE} = 40V, I_{B} = 0$ $V_{CE} = 50V, I_{B} = 0$: BDW23B 500 μΑ : BDW23C 500 μΑ Emitter Cut-off Current $V_{EB} = 5V$, $I_C = 0$ 2 I_{EBO} mΑ $V_{CE} = \overline{3V, I_C = 1A}$ * DC Current Gain 1000 h_{FE} $V_{CE} = 3V, I_{C} = 2A$ 20000 750 $V_{CE} = 3V, I_{C} = 6A$ 100 V_{CE}(sat) * Collector-Emitter Saturation Voltage $I_C = 2A, I_B = 8mA$ 2 ٧

 $I_{C} = 6A, I_{B} = 60mA$

 $I_C = 2A, I_B = 8mA$

 $V_{CE} = 3V, I_{C} = 1A$

 $V_{CE} = 3V$, $I_{C} = 6A$

 $I_F = 2A$

* Base-Emitter Saturation Voltage

* Base-Emitter ON Voltage

V_{BE}(sat)

V_{BE}(on)

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^{*} Parallel Diode Forward Voltage V_{F} * Pulse Test: PW =300µs, duty Cycle =1.5% Pulsed



Typical Characteristics

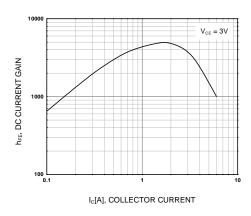


Figure 1. DC current Gain

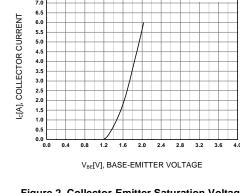


Figure 2. Collector-Emitter Saturation Voltage

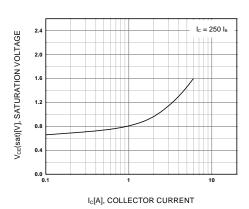


Figure 3. Base-Emitter On Voltage

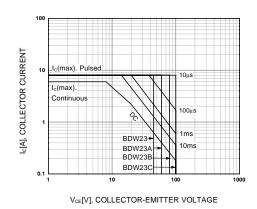


Figure 4. Safe Operating Area

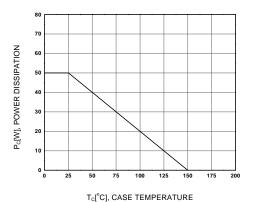
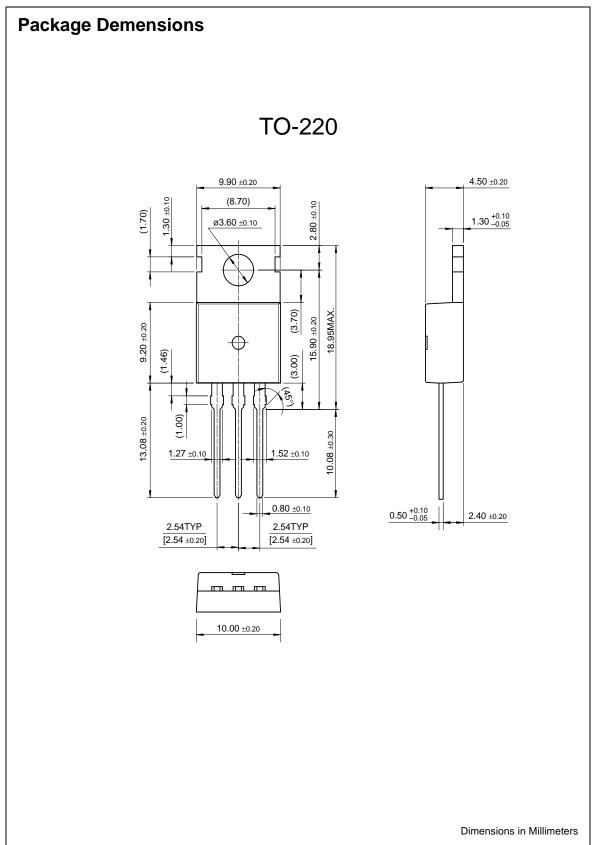


Figure 5. Power Derating

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